PBSS4041PT

60 V, 2.7 A PNP low VCEsat transistor

20 September 2024

Product data sheet

1. General description

PNP low V_{CEsat} transistor in a SOT23 small Surface-Mounted Device (SMD) plastic package.

NPN complement: PBSS4041NT

2. Features and benefits

- Very low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- High collector current gain (h_{FE}) at high I_C
- · High energy efficiency due to less heat generation
- Smaller required Printed-Circuit Board (PCB) area than for conventional transistors
- AEC-Q101 qualified

3. Applications

- Loadswitch
- · Battery-driven devices
- Power management
- · Charging circuits
- · Power switches (e.g. motors, fans)

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	-60	V
I _C	collector current		-	-	-2.7	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms	-	-	-8	Α
R _{CEsat}	collector-emitter saturation resistance	I_C = -3 A; I_B = -300 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	70	120	mΩ



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	3	С
2	Е	emitter		j
3	С	collector		В—
				 E
			SOT23	sym013

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PBSS4041PT	SOT23	plastic, surface-mounted package; 3 terminals; 1.9 mm pitch; 2.9 mm x 1.3 mm x 1 mm body	SOT23		

7. Marking

Table 4. Marking codes

Type number	Marking code[1]
PBSS4041PT	%BL

[1] % = placeholder for manufacturing site code

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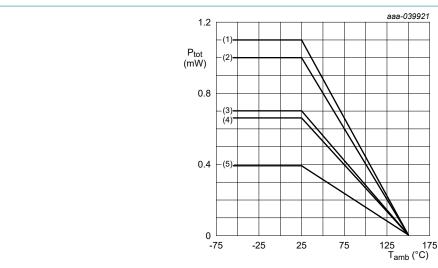
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	-60	V
V _{CEO}	collector-emitter voltage	open base		-	-60	V
V _{EBO}	emitter-base voltage	open collector		-	-5	V
I _C	collector current			-	-2.7	А
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-8	Α
I _B	base current			-	-1	А
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	0.39	W
			[2]	-	0.66	W
			[3]	-	0.7	W
			[4]	-	1	W
			[5]	-	1.1	W
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided, 35 µm copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided, 35 μm copper, tin-plated, mounting pad for collector 1 cm².
- [3] Device mounted on an FR4 PCB, 4-layer, tin-plated and standard footprint.
- [4] Device mounted on an FR4 PCB, 4-layer, tin-plated, mounting pad for collector 1 cm².
- [5] Device mounted on a ceramic PCB, Al₂O₃, single-sided, 35 μm copper, tin-plated and standard footprint.



- (1) Ceramic PCB, Al₂O₃, single-sided, 35 µm copper, standard footprint
- (2) FR4 PCB, 4-layer copper, 1 cm²
- (3) FR4 PCB, 4-layer copper, standard footprint
- (4) FR4 PCB, single-sided, 35 μm copper, 1 cm²
- (5) FR4 PCB, single-sided, 35 µm copper, standard footprint

Fig. 1. Power derating curves

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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)} thermal resistance to junction to ambient	thermal resistance from]]]	[1]	-	-	320	K/W
	junction to ambient		[2]	-	-	190	K/W
			[3]	-	-	180	K/W
			[4]	-	-	125	K/W
			[5]	-	-	115	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	62	K/W

- [1] Device mounted on an FR4 PCB, single-sided, 35 µm copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided, 35 μm copper, tin-plated, mounting pad for collector 1 cm².
- [3] Device mounted on an FR4 PCB, 4-layer, tin-plated and standard footprint.
- [4] Device mounted on an FR4 PCB, 4-layer, tin-plated, mounting pad for collector 1 cm².
- [5] Device mounted on a ceramic PCB, Al₂O₃, single-sided, 35 μm copper, tin-plated and standard footprint.

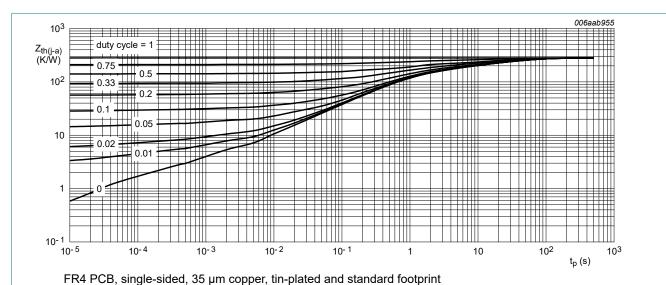
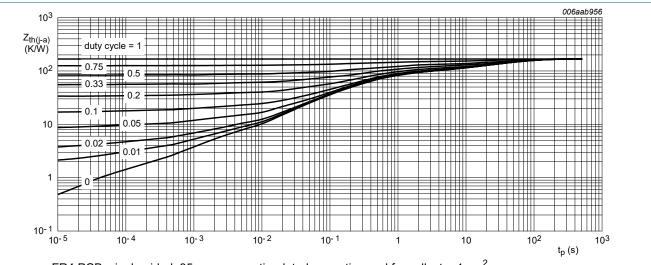


Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

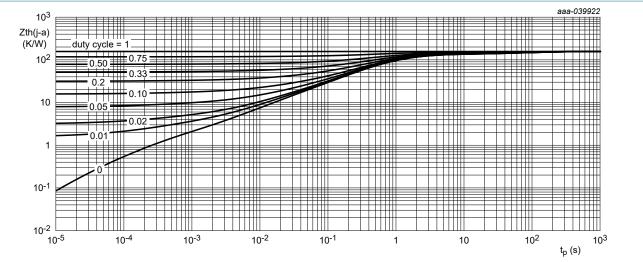


FR4 PCB, single-sided, 35 µm copper, tin-plated, mounting pad for collector 1 cm²

Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

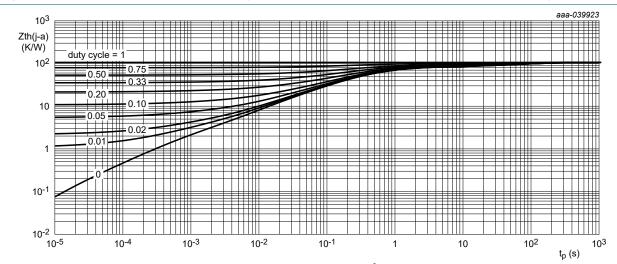
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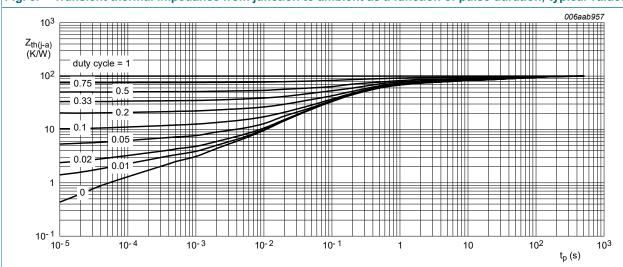
FR4 PCB, 4-layer, tin-plated and standard footprint

Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, 4-layer, tin-plated, mounting pad for collector 1 cm²

Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



Ceramic PCB, Al₂O₃, single-sided, 35 µm copper, tin-plated and standard footprint

Fig. 6. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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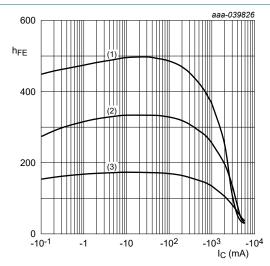
10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{(BR)CBO}	collector-base breakdown voltage	I_C = -100 μ A; I_E = 0 A; T_{amb} = 25 °C	-60	-	-	V
V _{(BR)CEO}	collector-emitter breakdown voltage	$I_C = -10 \text{ mA}; I_B = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	-60	-	-	V
V _{(BR)EBO}	emitter-base breakdown voltage	$I_E = -100 \ \mu A; I_C = 0 \ A; T_{amb} = 25 \ ^{\circ}C$	-5	-	-	V
I _{CBO}	collector-base cut-off	V _{CB} = -60 V; I _E = 0 A; T _{amb} = 25 °C	-	-	-100	nA
	current	V _{CB} = -60 V; I _E = 0 A; T _j = 150 °C	-	-	-55	μΑ
I _{CES}	collector-emitter cut-off current	V _{CE} = -48 V; V _{BE} = 0 V; T _{amb} = 25 °C	-	-	-100	nA
ЕВО	emitter-base cut-off current	V _{EB} = -5 V; I _C = 0 A; T _{amb} = 25 °C	-	-	-100	nA
h _{FE}	DC current gain	V_{CE} = -2 V; I_{C} = -500 mA; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	200	300	-	
		V_{CE} = -2 V; I_{C} = -1 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	150	260	-	
		V_{CE} = -2 V; I_{C} = -2 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	120	210	-	
		V_{CE} = -2 V; I_{C} = -4 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	35	90	-	
V _{CEsat}	collector-emitter saturation voltage	I_C = -500 mA; I_B = -50 mA; pulsed; $t_p \le$ 300 μs; $\delta \le$ 0.02; T_{amb} = 25 °C	-	-50	-75	mV
		I_C = -1 A; I_B = -10 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-265	-390	mV
		I_C = -1 A; I_B = -50 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-100	-150	mV
		I_C = -2 A; I_B = -40 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-390	-600	mV
		I_C = -3 A; I_B = -300 mA; pulsed; $t_p \le$	-	-205	-360	mV
R _{CEsat}	collector-emitter saturation resistance	300 μs; δ ≤ 0.02; T _{amb} = 25 °C	-	70	120	mΩ
V _{BEsat}	base-emitter saturation voltage	I_C = -1 A; I_B = -100 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-0.85	-1	V
		I_C = -3 A; I_B = -300 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-0.97	-1.15	V
V_{BE}	base-emitter voltage	V_{CE} = -2 V; I_{C} = -2 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02	-	-0.8	-0.9	V
d	delay time	V _{CC} = -12.5 V; I _C = -1 A; I _{Bon} = -50 mA;	-	20	-	ns
r	rise time	I _{Boff} = 50 mA; T _{amb} = 25 °C	-	45	-	ns
on	turn-on time		-	65	-	ns
·S	storage time		-	345	-	ns
f	fall time		-	75	-	ns
off	turn-off time		-	420	-	ns
f _T	transition frequency	V_{CE} = -10 V; I_{C} = -100 mA; f = 100 MHz; T_{amb} = 25 °C	-	135	-	MHz

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
C _c	collector capacitance	$V_{CB} = -10 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A};$	-	38	-	pF
		f = 1 MHz; T _{amb} = 25 °C				



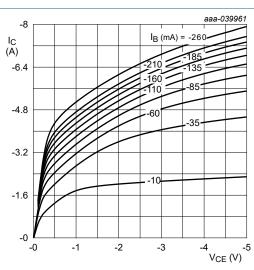
 V_{CE} = -2 V

(1) $T_{amb} = 100 \, ^{\circ}C$

(2) $T_{amb} = 25 \, ^{\circ}C$

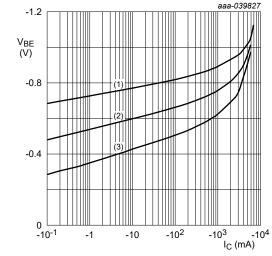
(3) $T_{amb} = -55 \, ^{\circ}C$

Fig. 7. DC current gain as a function of collector current; typical values



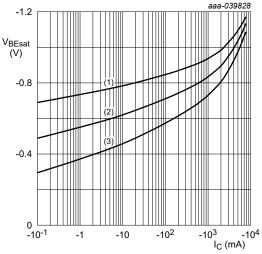
 T_{amb} = 25 °C

Fig. 8. Collector current as a function of collectoremitter voltage; typical values



V_{CE} = -2 V (1) T_{amb} = -55 °C (2) T_{amb} = 25 °C (3) T_{amb} = 100 °C

Base-emitter voltage as a function of collector Fig. 9. current; typical values



 $I_{C}/I_{B} = 20$ (1) $T_{amb} = -55 \,^{\circ}C$ (2) $T_{amb} = 25 \,^{\circ}C$ (3) $T_{amb} = 100 \,^{\circ}C$

Fig. 10. Base-emitter saturation voltage as a function of collector current; typical values

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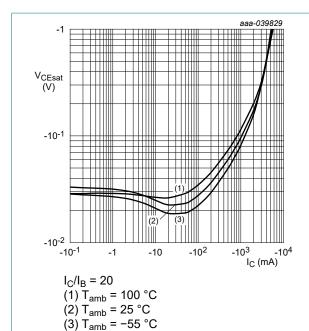


Fig. 11. Collector-emitter saturation voltage as a function of collector current; typical values

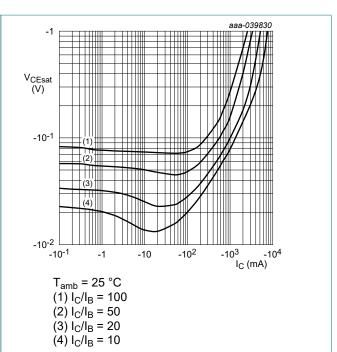


Fig. 12. Collector-emitter saturation voltage as a function of collector current; typical values

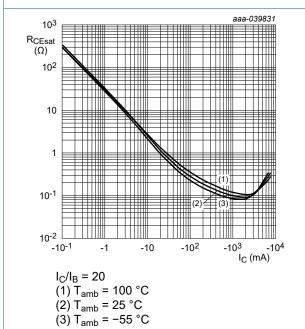
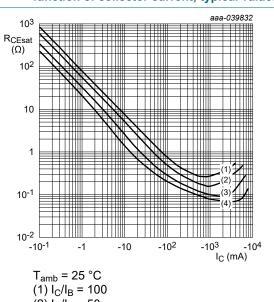


Fig. 13. Collector-emitter saturation resistance as a function of collector current; typical values



(1) $I_C/I_B = 100$ (2) $I_C/I_B = 50$ (3) $I_C/I_B = 20$ (4) $I_C/I_B = 10$

Fig. 14. Collector-emitter saturation resistance as a function of collector current; typical values

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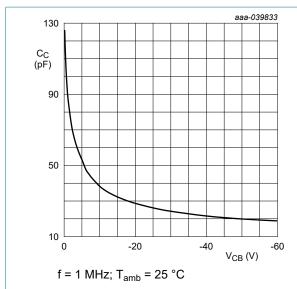
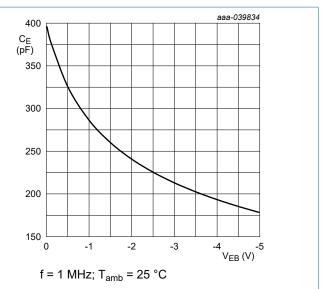


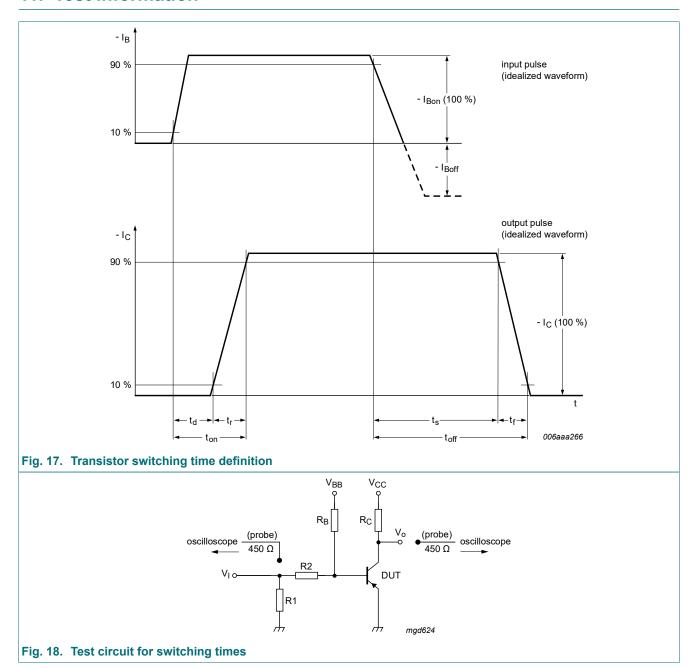
Fig. 15. Collector capacitance as a function of collector- Fig. 16. Emitter capacitance as a function of emitterbase voltage; typical values



base voltage; typical values

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11. Test information

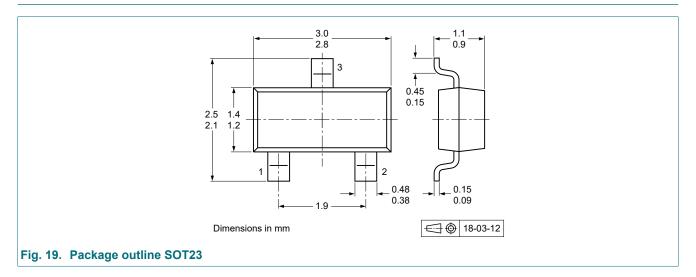


Quality information

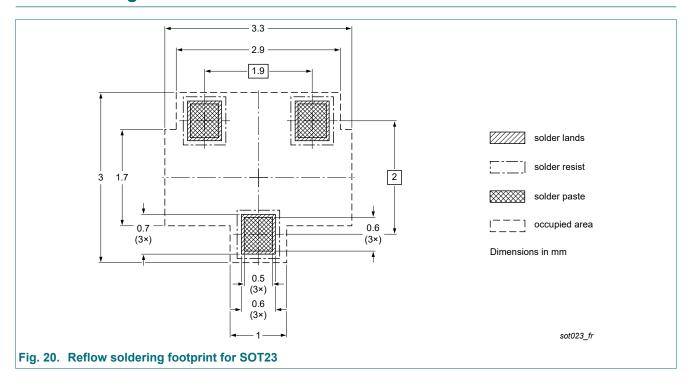
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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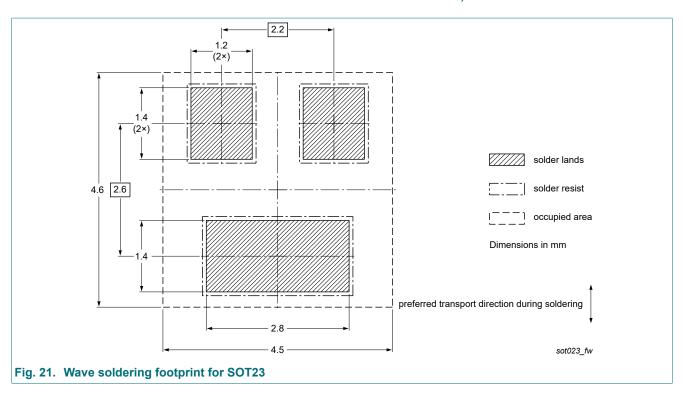
12. Package outline



13. Soldering



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14. Revision history

Table 8. Revision history

Table of Notician motory							
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes			
PBSS4041PT v.4	20240920	Product data sheet	-	PBSS4041PT v.3			
Modifications:	New graphics	added, graphs updated and v	alues changed.	·			
PBSS4041PT v.3	20230915	Product data sheet	-	PBSS4041PT_2			
PBSS4041PT_2	20100131	Product data sheet	-	PBSS4041PT_1			
PBSS4041PT_1	20100131	Product data sheet	-	-			

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15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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